

Description

The G86N03 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

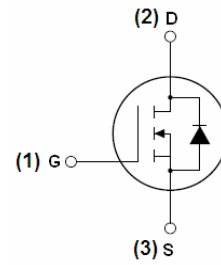
General Features

- | | | | |
|-----------|-----------------------------|-----------------------------|-------|
| V_{DSS} | $R_{DS(ON)}$
@ 4.5V(Typ) | $R_{DS(ON)}$
@ 10V (Typ) | I_D |
| 30V | 7.5 m Ω | 4.5 m Ω | 86A |

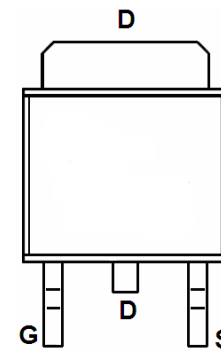
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

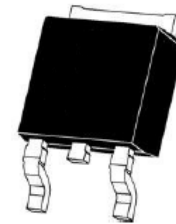
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



TO-252

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	86	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	50	A
Pulsed Drain Current	I_{DM}	170	A
Maximum Power Dissipation	P_D	83	W
Derating factor		0.56	W/ $^{\circ}C$
Single pulse avalanche energy	E_{AS}	306	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.8	$^{\circ}\text{C}/\text{W}$
--	-----------------	-----	-----------------------------

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	4.5	6.5	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	7.5	10.5	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=24A$	20	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	2330	-	PF
Output Capacitance	C_{oss}		-	460	-	PF
Reverse Transfer Capacitance	C_{rss}		-	230	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=30A$ $V_{GS}=10V, R_{GEN}=2.7\Omega$	-	20	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=30A,$ $V_{GS}=10V$	-	51	-	nC
Gate-Source Charge	Q_{gs}		-	14	-	nC
Gate-Drain Charge	Q_{gd}		-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=15A$	-	-	1	V
Diode Forward Current ^(Note 2)	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = 80A$ $di/dt = 100A/\mu s$ ^(Note 3)	-	32	50	nS
Reverse Recovery Charge	Q_{rr}		-	12	20	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

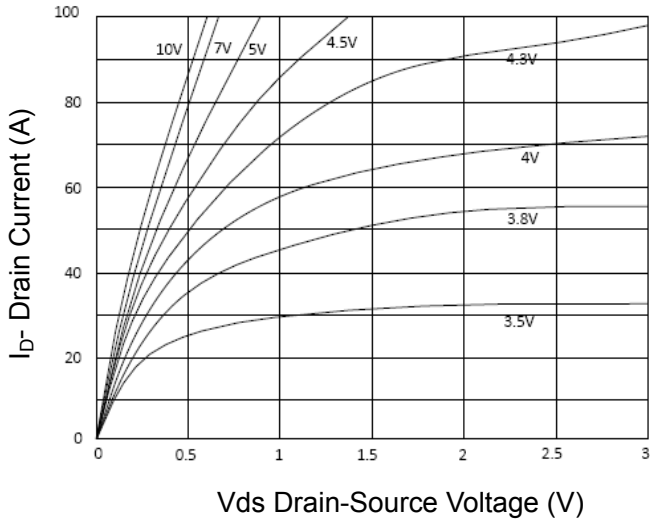


Figure 1 Output Characteristics

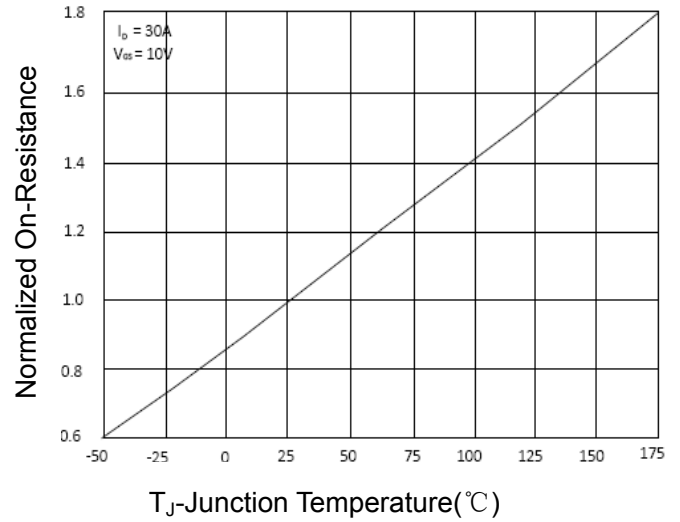


Figure 4 R_{dson} -Junction Temperature

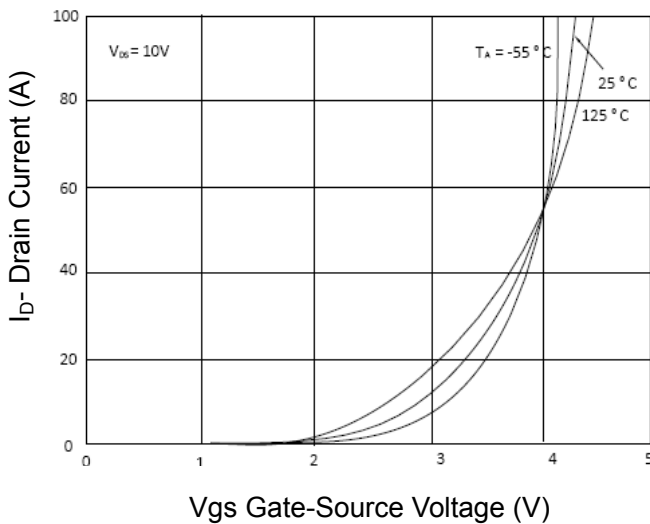


Figure 2 Transfer Characteristics

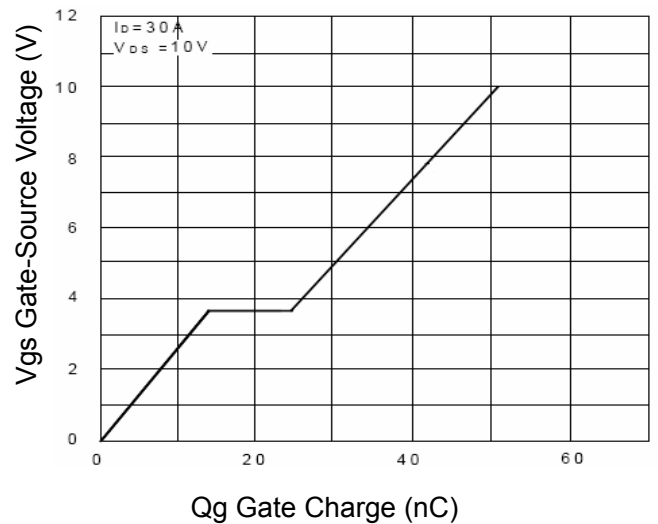


Figure 5 Gate Charge

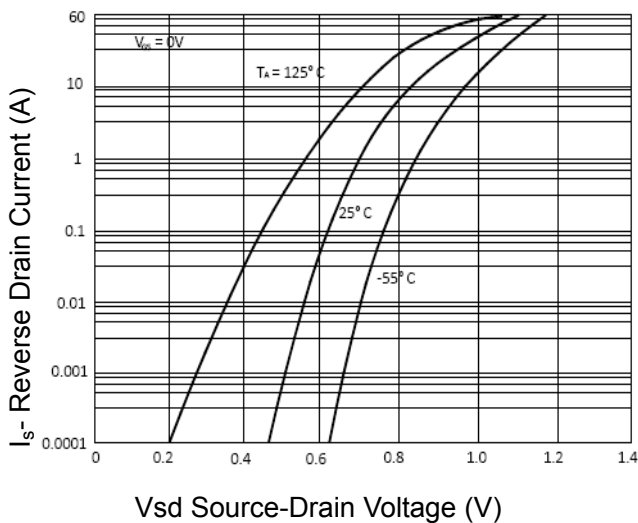


Figure 3 Source- Drain Diode Forward

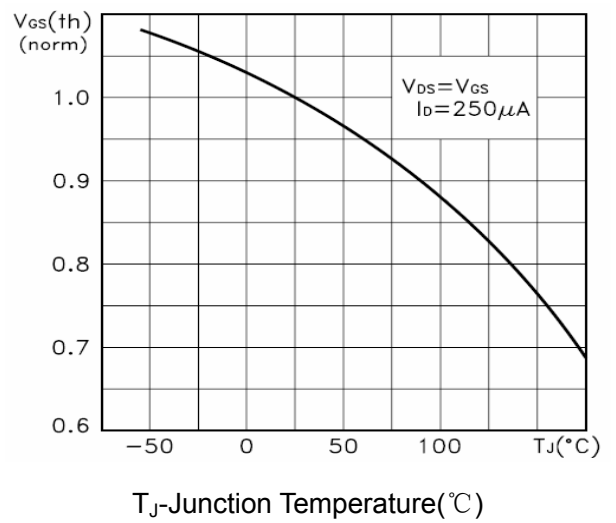
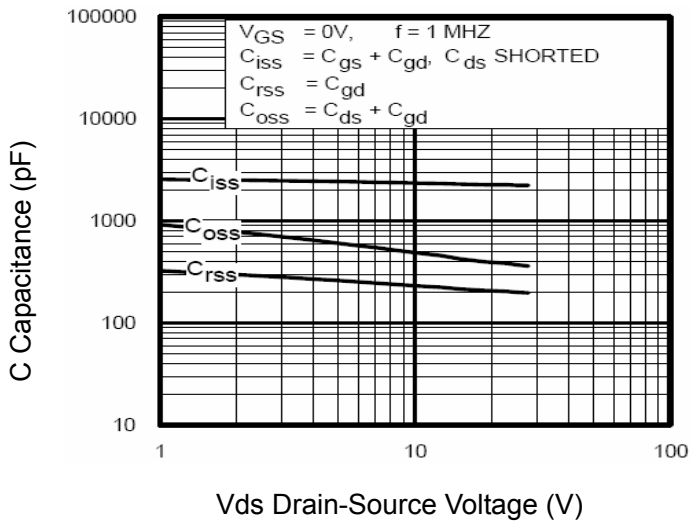
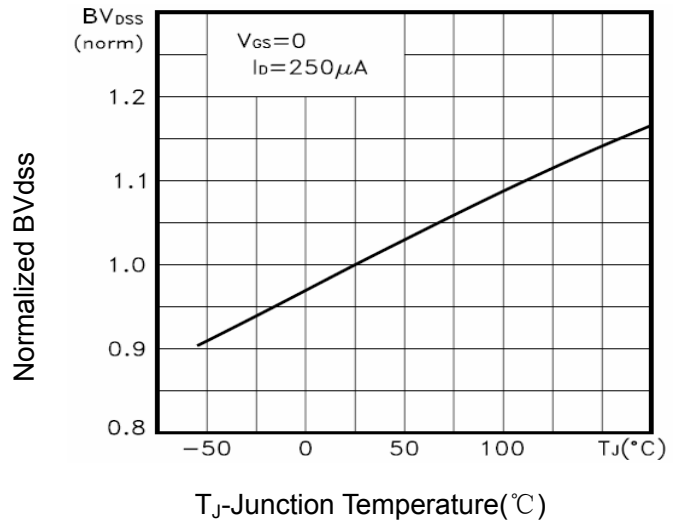


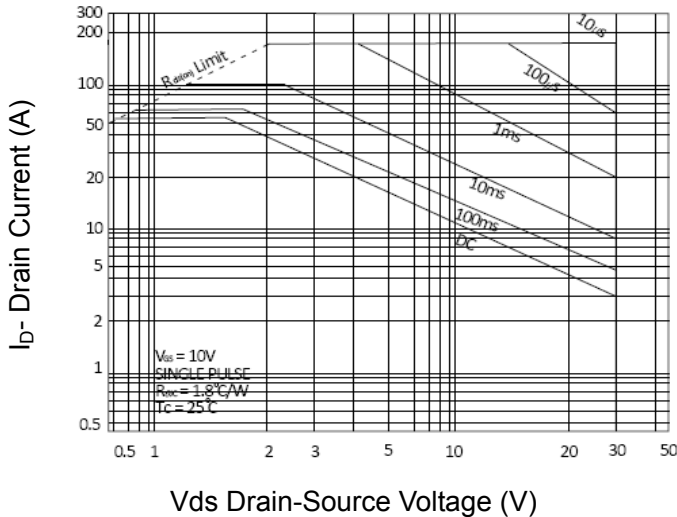
Figure 6 $V_{GS(th)}$ vs Junction Temperature



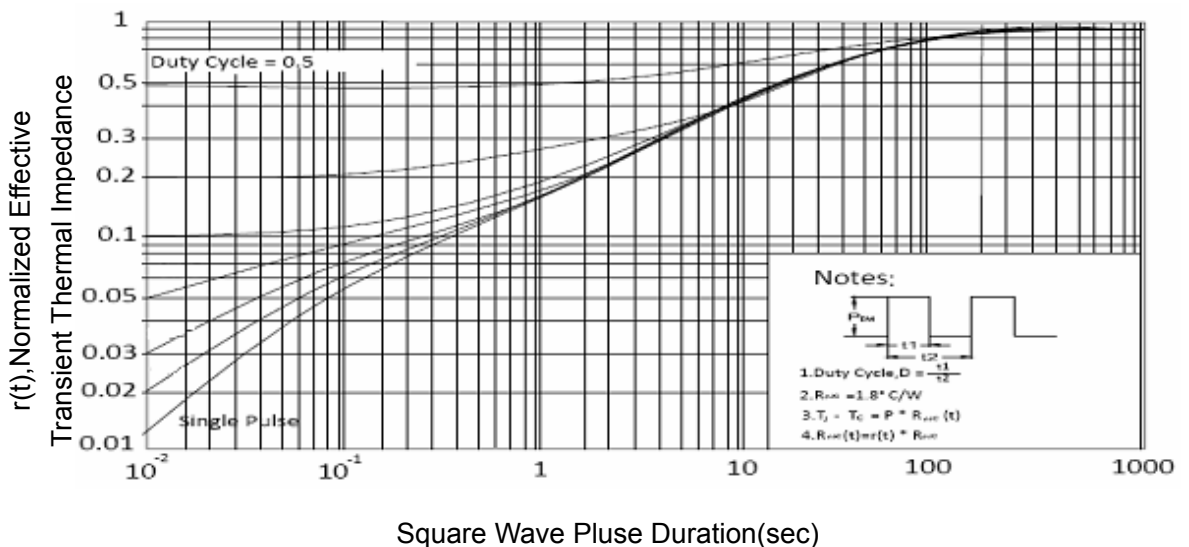
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



T_J -Junction Temperature($^{\circ}C$)
Figure 9 BV_{DSS} vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



Square Wave Pulse Duration(sec)
Figure 10 Normalized Maximum Transient Thermal Impedance

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [GOFORD](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#)
[WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTGR](#) [DMNH15H110SK3-13](#)
[SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#) [IPA60R230P6](#)